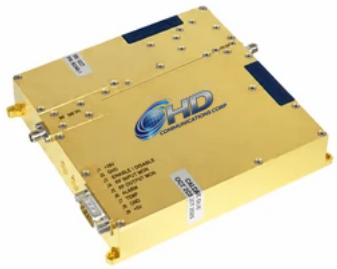
HD31113
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear GaAsFET hybrid design
Instantaneous wide bandwidth
Suitable for all single channel modulations standards
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	18.0 - 26.5 GHz	
Power Output	5 Watt Min	CW
Power Gain	37 dB Min	
Power Gain Flatness	4.0 dB p-p Max	Constant input power
Input / Output Return Loss	10 dB Min	Relative to 50 Ohm
Harmonics	>20 dBc Typ	At rated Pout
Non Harmonics Spurious	>60 dBc Min	
Operating Voltage	9.0 ± 0.5 VDC Nom	
Current Consumption	10.0 Amp Max	At rated Pout
Max Input Power	+10 dBm	Without damage
Load VSWR Protection	∞ : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	135 X 135 X 27 mm	Excluding connectors
Weight	TBD	
RF Connectors In/Out	SMA female	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

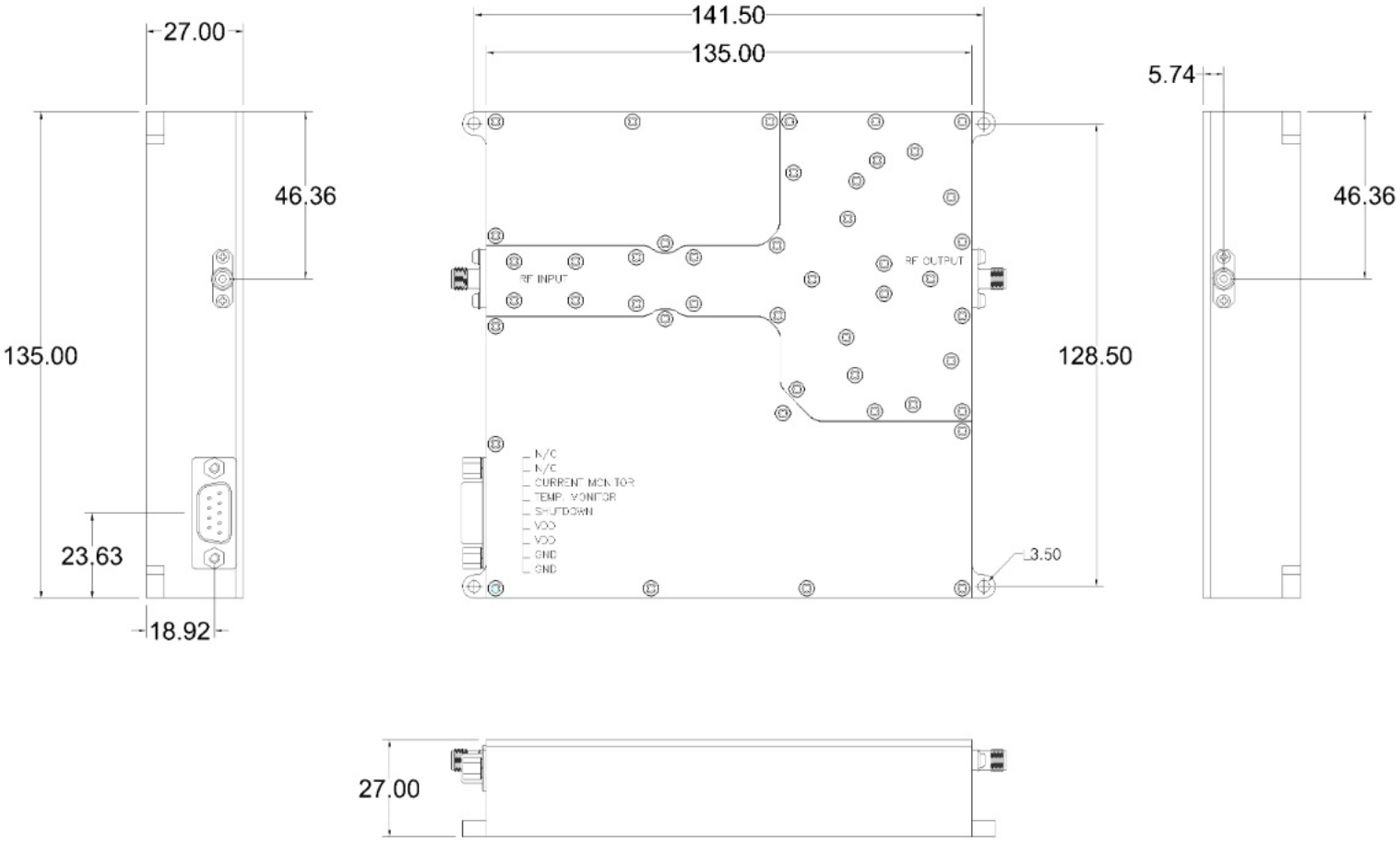
D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	Reserved
2	N/C	Reserved
3	CURRENT SENSOR	I_D@**100mV**/100mA Typ
4	TEMP SENSOR	V_T@10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
6, 7	VDD	9VDC
8, 9	GND	Ground

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Specifications subject to change without notice. Specifications and drawings may vary with selected options.

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OUTLINE DRAWING



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